4 BIT D TYPE LATCH

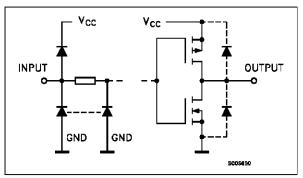
- HIGH SPEED
 - $t_{PD} = 10 \text{ ns} (TYP.) AT V_{CC} = 5 \text{ V}$
- LOW POWER DISSIPATION $I_{CC} = 2 \mu A \text{ (MAX.)} \text{ AT } T_A = 25 \text{ °C}$
- HIGH NOISE IMMUNITY

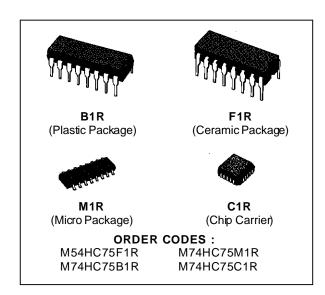
 VNIH = VNIL = 28 % VCC (MIN.)
- OUTPUT DRIVE CAPABILITY 10 LSTTL LOADS
- SYMMETRICAL OUTPUT IMPEDANCE | IOH | = I_{OL} = 4 mA (MIN.)
- BALANCED PROPAGATION DELAYS tplh = tphl
- WIDE OPERATING VOLTAGE RANGE Vcc = (OPR) = 2 V TO 6 V
- PIN AND FUNCTION COMPATIBLE WITH 54/74LS75

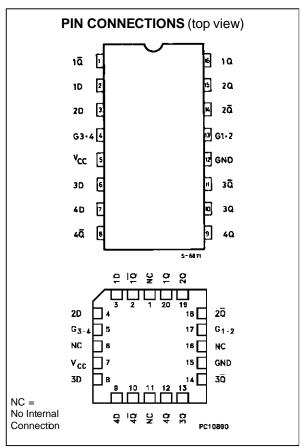
DESCRIPTION

The M54/74HC75 is a high speed CMOS 4-BIT D-TYPE LATCH fabricated in silicon gate C²MOS technology. It has the same high speed performance of LSTTL combined with true CMOS low power consumption. It contains two groups of 2-bit latches controlled by an enable input (G1•2 or G3•4). These two latch groups can be used in different circuits. Each latch has Q and \overline{Q} outputs (1Q - $4\overline{Q}$ and 1Q - $4\overline{Q}$). The data applied to the data input is transferred to the Q and \overline{Q} outputs when the enable input is taken high and the outputs will follow the data input as long as the enable input is kept high. When the enable input is taken low, the information data applied to the data input is retained at the outputs. All inputs are equipped with protection circuits against static discharge and transient excess voltage.

INPUT AND OUTPUT EQUIVALENT CIRCUIT







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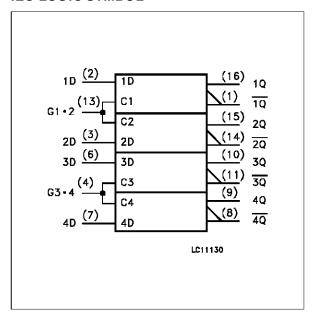
TRUTH TABLE

INP	UTS	OUTI	PUTS	FUNCTION
D	G	Q	Q	TONCTION
L	Н	L	Н	
Н	Н	Н	L	
Х	L	Qn		LATCH

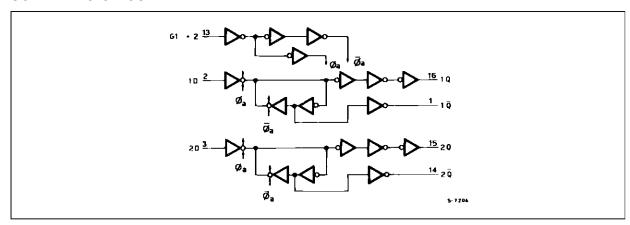
PIN DESCRIPTION

PIN No	SYMBOL	NAME AND FUNCTION
1, 14, 11, 8	$1\overline{Q}$ to $4\overline{Q}$	Complementary Latch
		Outputs
2, 3, 6, 7	1D to 4D	Data Inputs
4	G3 • 4	Latch Enable Input, latches 3 and 4
13	G1 • 2	Latch Enable Input, latches 1 and 2
16, 15, 10, 9	1Q to 4Q	Latch Outputs
12	GND	Ground (0V)
5	Vcc	Positive Supply Voltage

IEC LOGIC SYMBOL



SCHEMATIC CIRCUIT



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
Vcc	Supply Voltage	-0.5 to +7	V
VI	DC Input Voltage	-0.5 to V _{CC} + 0.5	V
Vo	DC Output Voltage	-0.5 to V _{CC} + 0.5	V
l _{IK}	DC Input Diode Current	± 20	mA
I _{OK}	DC Output Diode Current	± 20	mA
lo	DC Output Source Sink Current Per Output Pin	± 25	mA
lcc or I _{GND}	DC V _{CC} or Ground Current	± 50	mA
P_{D}	Power Dissipation	500 (*)	mW
T _{stg}	Storage Temperature	-65 to +150	°C
TL	Lead Temperature (10 sec)	300	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these condition is not implied. (*) 500 mW: ≡ 65 °C derate to 300 mW by 10mW/°C: 65 °C to 85 °C



RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit	
V_{CC}	Supply Voltage		2 to 6	V
V_{I}	Input Voltage		0 to V _{CC}	V
Vo	Output Voltage		0 to V _{CC}	V
T_{op}	Operating Temperature: M54HC Series M74HC Series		-55 to +125 -40 to +85	°C
t _r , t _f	Input Rise and Fall Time	V _{CC} = 2 V	0 to 1000	ns
		$V_{CC} = 4.5 \text{ V}$	0 to 500	
		$V_{CC} = 6 V$	0 to 400	

DC SPECIFICATIONS

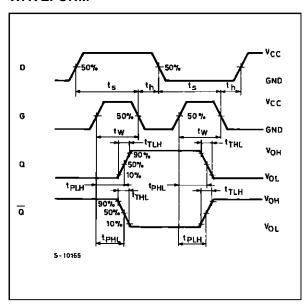
		Test Conditions		Value								
Symbol	Parameter	V _{CC} (V)			T _A = 25 °C 54HC and 74HC			-40 to 85 °C 74HC		-55 to 125 °C 54HC		Unit
		()			Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
V_{IH}	High Level Input	2.0			1.5			1.5		1.5		
	Voltage	4.5			3.15			3.15		3.15		V
		6.0			4.2			4.2		4.2		
V_{IL}	Low Level Input	2.0					0.5		0.5		0.5	
	Voltage	4.5					1.35		1.35		1.35	V
		6.0					1.8		1.8		1.8	
V_{OH}	High Level	2.0	VI =		1.9	2.0		1.9		1.9		
	Output Voltage	4.5	VI –	I _O =-20 μA	4.4	4.5		4.4		4.4		
		6.0	or		5.9	6.0		5.9		5.9		V
		4.5	VIL	I _O =-4.0 mA	4.18	4.31		4.13		4.10		
		6.0		I _O =-5.2 mA	5.68	5.8		5.63		5.60		
V_{OL}	Low Level Output	2.0	Vı =			0.0	0.1		0.1		0.1	
	Voltage	4.5	VIH	I _O = 20 μA		0.0	0.1		0.1		0.1	.,
		6.0	or			0.0	0.1		0.1		0.1	V
		4.5	V_{IL}	I _O = 4.0 mA		0.17	0.26		0.33		0.40	
		6.0		I _O = 5.2 mA		0.18	0.26		0.33		0.40	
lı	Input Leakage Current	6.0	V _I = '	V _{CC} or GND			±0.1		±1		±1	μΑ
Icc	Quiescent Supply Current	6.0	V _I = '	V _{CC} or GND			2		20		40	μΑ

AC ELECTRICAL CHARACTERISTICS ($C_L = 50 \text{ pF}$, Input $t_r = t_f = 6 \text{ ns}$)

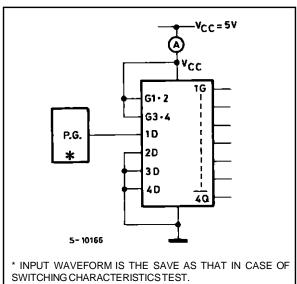
		Test Conditions				Value				
Symbol	Parameter	Vcc (V)	T _A = 25 °C 54HC and 74HC			-40 to 85 °C 74HC		-55 to 125 °C 54HC		Unit
		(V)	Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
t _{TLH}	Output Transition	2.0		25	75		95		110	
t _{THL}	Time	4.5		7	15		19		22	ns
		6.0		6	13		16		19	
t _{PLH}	Propagation	2.0		36	110		140		165	
t _{PHL}	Delay Time	4.5		12	22		28		33	ns
	(DATA-Q)	6.0		10	19		24		28	
t _{PLH}	Propagation	2.0		40	125		155		190	
t _{PHL}		4.5		13	25		31		38	ns
	(G-Q)	6.0		11	21		26		32	
t _{W(H)}	Minimum Pulse	2.0		18	75		95		110	
	Width (G)	4.5		6	15		19		22	ns
		6.0		6	13		16		19	
ts	Minimum Set-up	2.0			50		65		75	
	Time	4.5			10		13		15	ns
		6.0			9		11		13	
t _h	Minimum Hold	2.0			25		30		40	
	Time	4.5			5		6		8	ns
		6.0			4		5		7	
C _{IN}	Input Capacitance			5	10		10		10	pF
C _{PD} (*)	Power Dissipation Capacitance			30						pF

^(*) CPD is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operting current can be obtained by the following equation. Icc(opr) = CPD ◆Vcc ◆fIN + Icc

SWITCHING CHARACTERISTICS TEST WAVEFORM

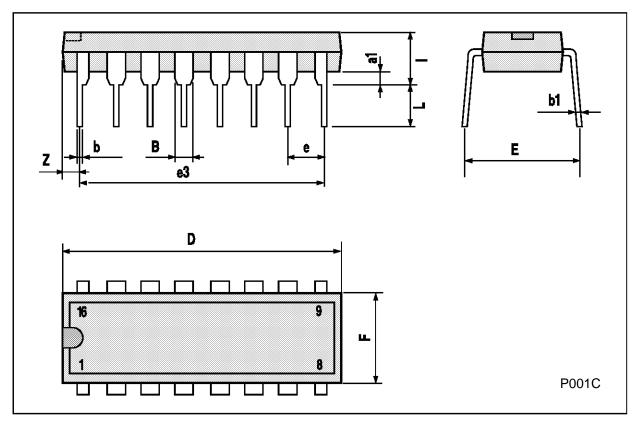


TEST CIRCUIT ICC (Opr)



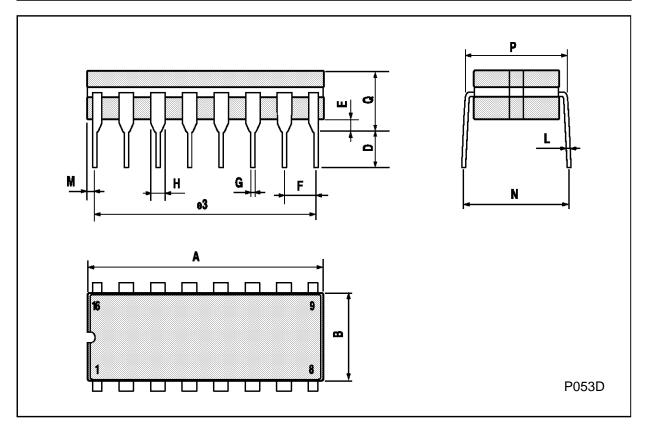
Plastic DIP16 (0.25) MECHANICAL DATA

DIM.		mm		inch				
Diwi.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.		
a1	0.51			0.020				
В	0.77		1.65	0.030		0.065		
b		0.5			0.020			
b1		0.25			0.010			
D			20			0.787		
E		8.5			0.335			
е		2.54			0.100			
e3		17.78			0.700			
F			7.1			0.280		
I			5.1			0.201		
L		3.3			0.130			
Z			1.27			0.050		



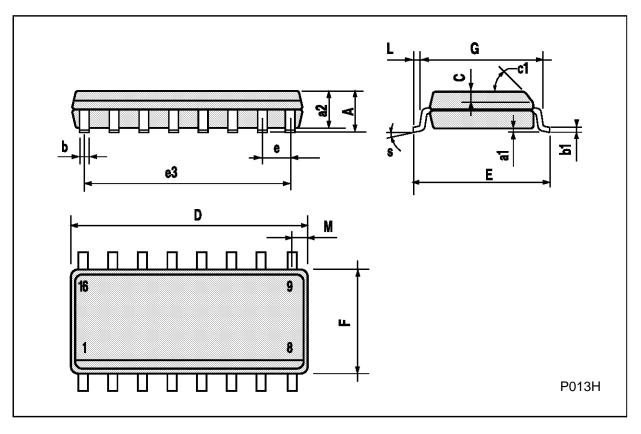
Ceramic DIP16/1 MECHANICAL DATA

DIM.		mm		inch				
D	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.		
А			20			0.787		
В			7			0.276		
D		3.3			0.130			
Е	0.38			0.015				
e3		17.78			0.700			
F	2.29		2.79	0.090		0.110		
G	0.4		0.55	0.016		0.022		
Н	1.17		1.52	0.046		0.060		
L	0.22		0.31	0.009		0.012		
М	0.51		1.27	0.020		0.050		
N			10.3			0.406		
Р	7.8		8.05	0.307		0.317		
Q			5.08			0.200		



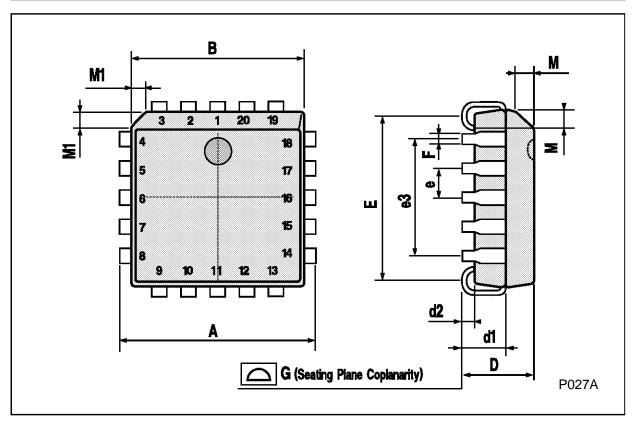
SO16 (Narrow) MECHANICAL DATA

DIM.		mm			inch			
Diwi.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.		
Α			1.75			0.068		
a1	0.1		0.2	0.004		0.007		
a2			1.65			0.064		
b	0.35		0.46	0.013		0.018		
b1	0.19		0.25	0.007		0.010		
С		0.5			0.019			
c1			45°	(typ.)				
D	9.8		10	0.385		0.393		
Е	5.8		6.2	0.228		0.244		
е		1.27			0.050			
e3		8.89			0.350			
F	3.8		4.0	0.149		0.157		
G	4.6		5.3	0.181		0.208		
L	0.5		1.27	0.019		0.050		
М			0.62			0.024		
S			8° (ı	max.)				



PLCC20 MECHANICAL DATA

DIM.		mm		inch				
5	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.		
А	9.78		10.03	0.385		0.395		
В	8.89		9.04	0.350		0.356		
D	4.2		4.57	0.165		0.180		
d1		2.54			0.100			
d2		0.56			0.022			
E	7.37		8.38	0.290		0.330		
е		1.27			0.050			
e3		5.08			0.200			
F		0.38			0.015			
G			0.101			0.004		
М		1.27			0.050			
M1		1.14			0.045			



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